

Ordering number : ENN0000

P-Channel Silicon MOSFET

CPH6324

Ultrahigh-Speed Switching Applications

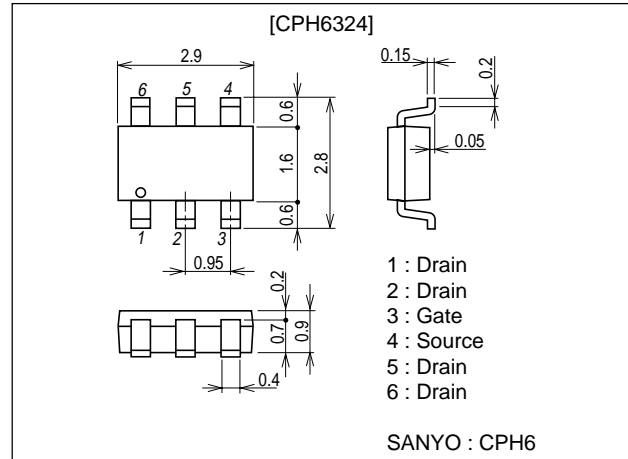
Preliminary

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Package Dimensions

unit : mm
2151A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-60	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		-2	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-8	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1200mm ² X0.8mm)	1.6	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA$, $V_{GS} = 0$	-60			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V$, $V_{GS} = 0$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16V$, $V_{DS} = 0$			± 10	μA
Gate-to-Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V$, $I_D = -1mA$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10V$, $I_D = -1A$	1.6	2.4		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -1A$, $V_{GS} = -10V$		275	360	$m\Omega$
	$R_{DS(on)2}$	$I_D = -1A$, $V_{GS} = -4V$		400	560	$m\Omega$

Marking : YA

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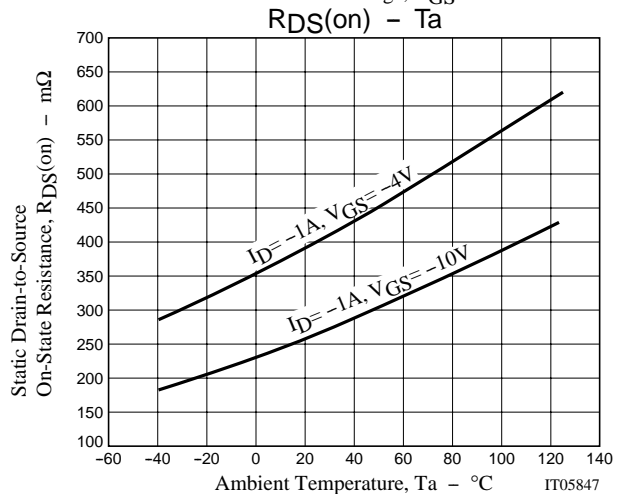
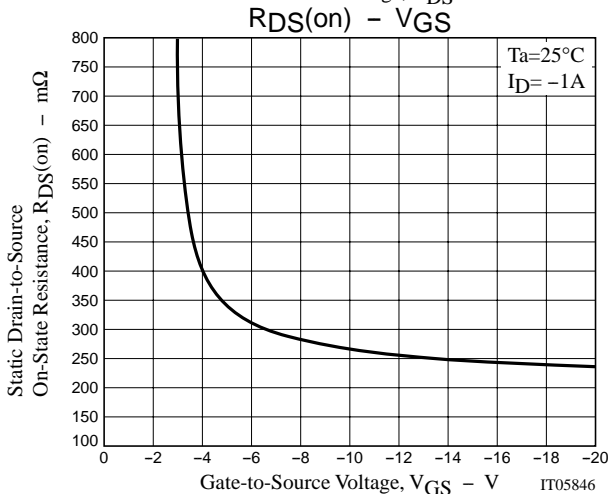
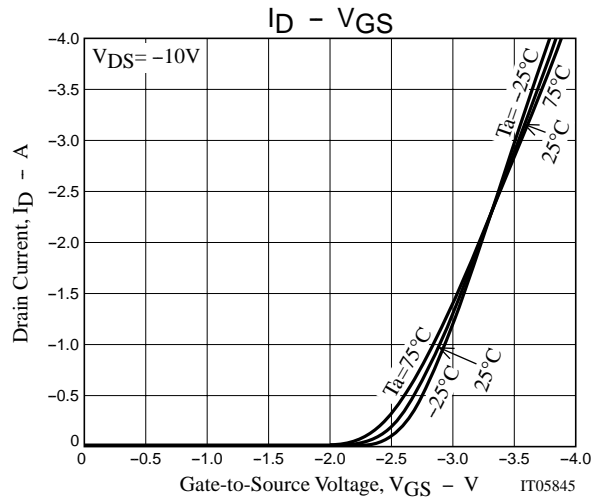
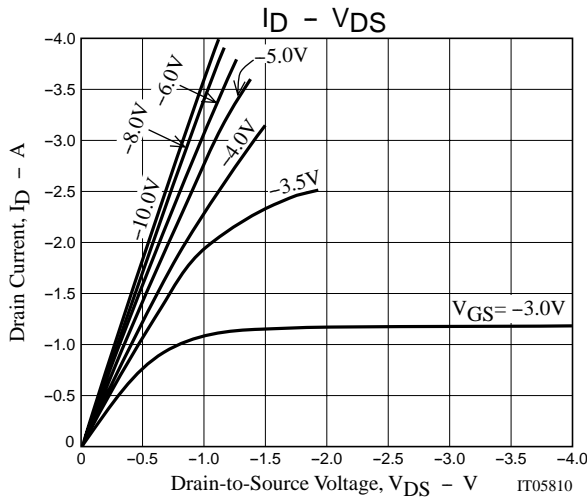
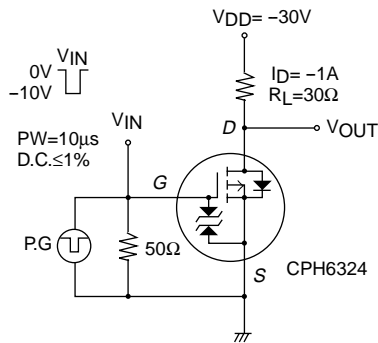
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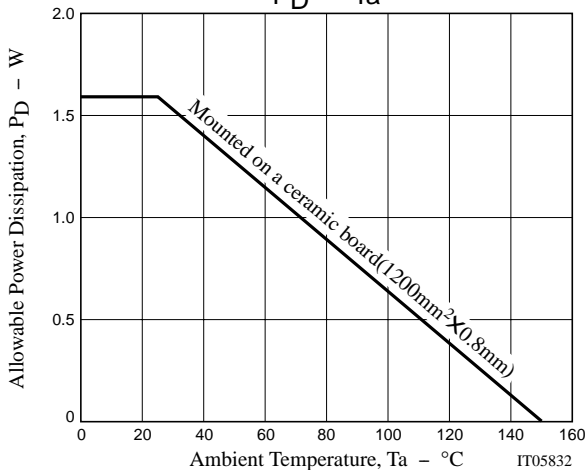
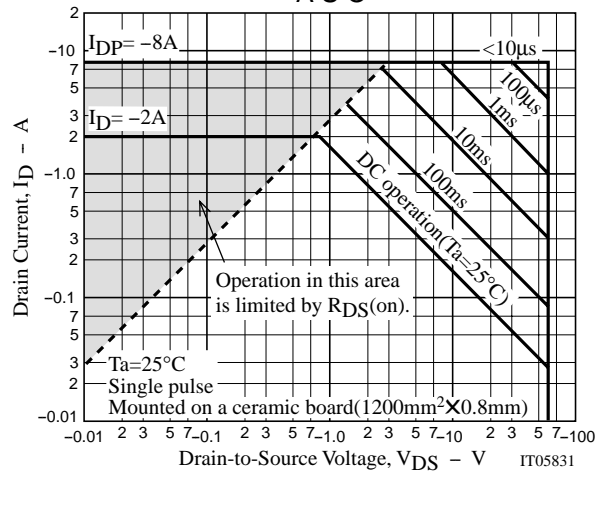
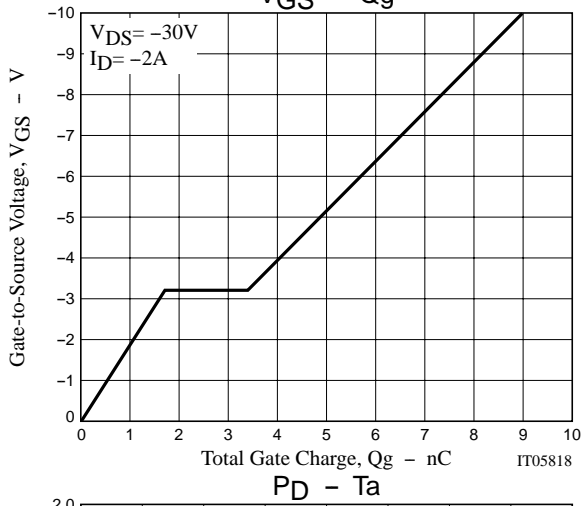
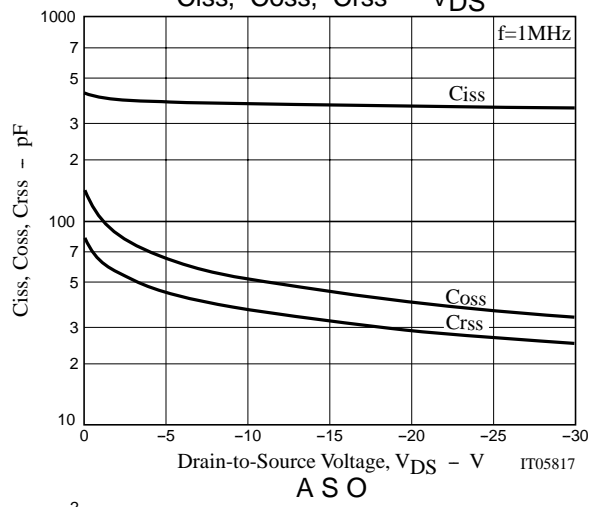
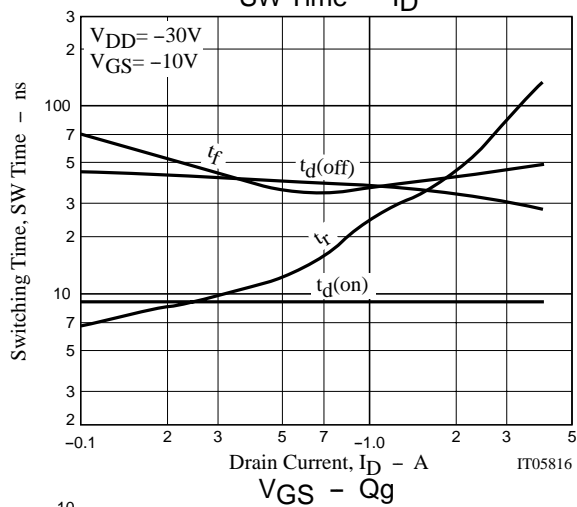
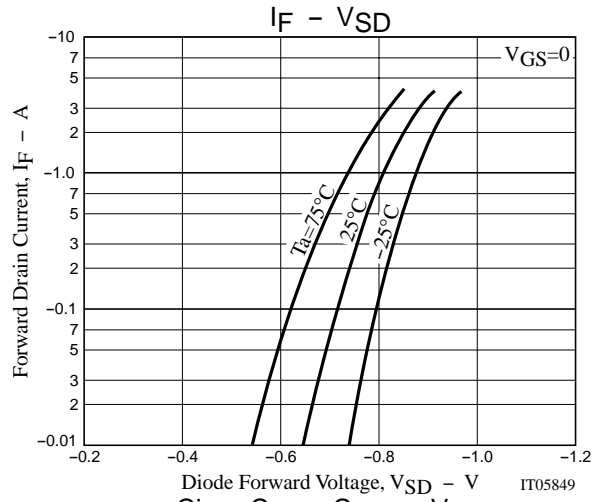
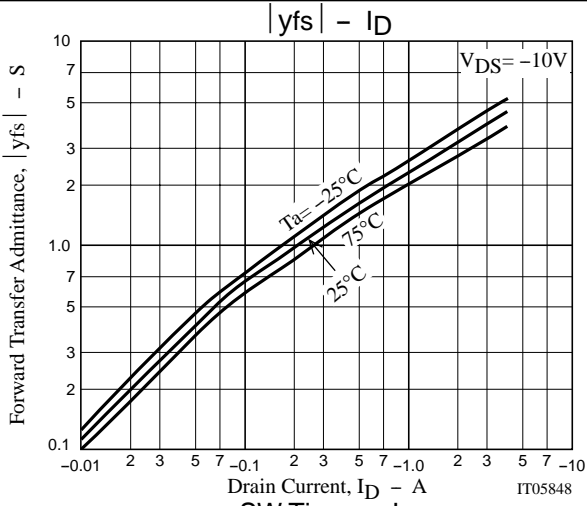
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =-20V, f=1MHz		365		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		39		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-20V, f=1MHz		30		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		9		ns
Rise Time	t _r	See specified Test Circuit.		24		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		38		ns
Fall Time	t _f	See specified Test Circuit.		38		ns
Total Gate Charge	Q _g	V _{DS} =-30V, V _{GS} =-10V, I _D =-2A		9		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =-30V, V _{GS} =-10V, I _D =-2A		1.7		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =-30V, V _{GS} =-10V, I _D =-2A		1.7		nC
Diode Forward Voltage	V _{SD}	I _S =-2A, V _{GS} =0	-0.84		-1.2	V

Switching Time Test Circuit



CPH6324



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